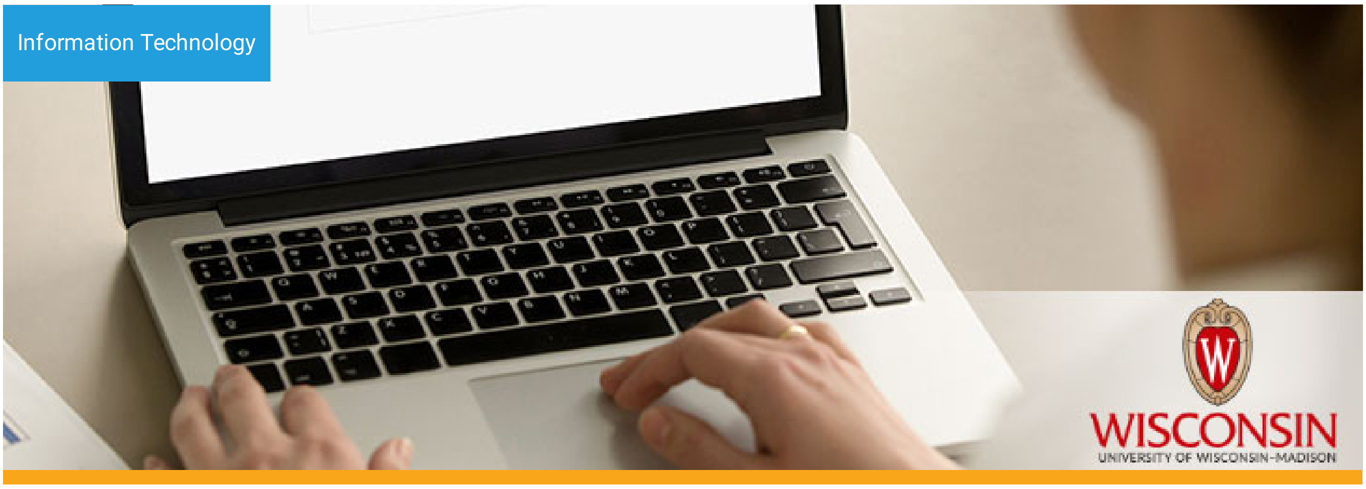

Non-Collinear Antiferromagnets For High Density And Low Power Spintronics Devices

View U.S. Patent No. 10,804,459 in PDF format.

WARF: P190064US01

Inventors: Chang-Beom Eom, Tianxiang Nan

The Invention

Spintronic devices based on metallic antiferromagnets having a non-collinear spin structure are provided. Also provided are methods for operating the devices. The spintronic devices are based on a bilayer structure that includes a spin torque layer of an antiferromagnetic material having a non-collinear triangular spin structure adjoining a layer of ferromagnetic material.

Additional Information

For More Information About the Inventors

- Chang-Beom Eom

Tech Fields

- Information Technology : Hardware
- Materials & Chemicals : Composites

For current licensing status, please contact Michael Carey at mcarey@warf.org or 608-960-9867